



GigaBit Logic

**16G061A**  
 ADVANCE

T-52-07

## Dual High Speed Pin Driver

### 1.5 GHz Operating Frequency

#### FEATURES

- DC to 1.5 GHz operation
- 600 ps propagation delay (ECL/GaAs)
- 150 ps output rise and fall times (ECL/GaAs)
- 200 ps output rise and fall times for up to 5Vp-p
- Adjustable output edge rate from 150 ps to 2000 ps
- Programmable output voltages up to 5.5 Vp-p over -2.5V to +5.5V range
- 100 mA output current drive capability
- High impedance, three state output control
- High speed ECL/GaAs compatible differential inputs
- On chip VBBS (-1.2V) reference voltage
- Available in C-leaded or leadless chip carriers or in die form. Packages contain internal decoupling capacitors for optimum high frequency performance
- Packaged parts available in 50Ω series terminated or unterminated (Rs=8Ω) configurations

#### APPLICATIONS

- ATE pin driver
- Laser driver
- Differential Line Receiver
- Switch Driver
- Level comparator
- Precision Pulse Generator
- CRT preamplifier
- General purpose driver

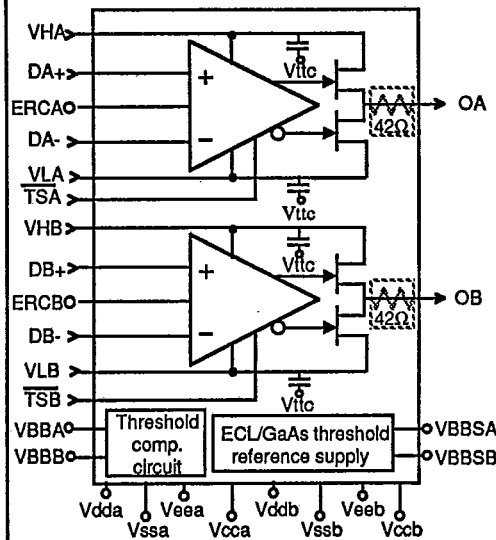
#### FUNCTIONAL DESCRIPTION

The 16G061A is a dual pin driver designed for use in very high speed GaAs/ECL as well as TTL/CMOS logic test systems. The A and B drivers of the 16G061A are electrically independent and have separate power supplies. Under control of the differential inputs, the output is switched between the levels provided on the VH (V High) and VL (V Low) inputs. The differential inputs can be driven with ECL or GaAs levels. The 16G061A has an on-chip threshold voltage generator (VBBS). When VBBS is connected to the D- inputs, the D+ inputs of the 16G061A can be driven single-ended. The VHigh output level is adjustable from -1.1V to +5.5V and the VLow output level can be adjusted from -2.5V to +1.5V. The output amplitude extends to 5.5Vp-p. Controls are provided (TSA, TSB) to force the outputs into a high impedance, three state condition. External unity gain amplifiers such as the LM324 or higher current operational amplifiers such as the LM759 can be used to buffer the VHigh (VH) and VLow (VL) inputs when driven from DACs.

The 16G061A features a continuously variable Edge Rate Control (ERCA and ERCB) to vary the output rise and fall times. Rise and fall times are typically 150 ps for a 1V peak to peak output (GaAs/ECL) and 200 ps for a 5V peak to peak output when Edge Rate Control (ERC) is biased at VSS. This translates to a slew rate of 6.5V/ns for a 1V output and 25V/ns for a 5V output. Rise and fall times can be increased to 2ns for a 5V peak to peak output by connecting ERC to VEE. This translates to a slew rate of 2.5V/ns for a 5V output. Between -5.1V and -4.8V the Edge Rate Control varies the edge rate at approximately 2 ps/mV for an ECL output swing and 3.5 ps/mV for a TTL output swing. System timing requirements are achieved through a specified 500ps driver propagation delay for ECL/GaAs levels, 600 ps delay for fast edge rate TTL/CMOS levels and 1.5 ns delay for slow edge rate TTL/CMOS levels.

The 16G061A is fabricated using GigaBit's high volume GaAs MESFET processing technology.

#### BLOCK DIAGRAM



#### 16G061A ORDERING INFORMATION

| Package Type               | Speed (Min. 25°C)          |                            |
|----------------------------|----------------------------|----------------------------|
|                            | 1.5 GHz                    |                            |
| C-leaded CC<br>Leadless CC | Unterminated               | 50Ω Terminated             |
|                            | 16G061A-UCE<br>16G061A-ULE | 16G061A-TOE<br>16G061A-TLE |
| Die                        | 16G061A-XE                 |                            |

\*Option T: 42Ω series resistor in the package;  
Rs=42+8=50Ω



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### ABSOLUTE MAXIMUM RATINGS

(Beyond which useful life may be impaired) (Notes 1, 4)

| SYMBOL | PARAMETER  | ABSOLUTE MAXIMUM RATINGS | NOTES |
|--------|--|--------------------------|-------|
| TSTOR  | Storage Temperature  | -65°C to +150°C          |       |
| TJ     | Junction Temperature   | -55°C to +150°C          |       |
| TC     | Case Temperature Under Bias  | -55°C to +125°C          | 2     |
| VDD    | Output Driver Gnd Supply   | VSS to +1.0 V            |       |
| VSS    | Supply Voltage   | -4.0 V to +0.5 V         |       |
| VEE    | Supply Voltage   | -7.0 V to VSS + 0.5 V    |       |
| VCC    | Supply Voltage   | +0.5 V to +10.0 V        |       |
| VIN    | Voltage Applied to Any Input; Continuous<br>VSS = -3.4 V, VEE = -5.2 V | -4.0 V to +0.5 V         |       |
| IIN    | Current Into Any Input; Continuous                                     | -0.5 mA to 1.0 mA        | 3     |
| VOUT   | Voltage Applied to Any Output  | VL to VL+7.0 V           | 5     |
| IOUT   | Current From Any Output; Continuous                                    | -150 mA                  |       |
| PD     | Power Dissipation Per Output<br>POUT = (VDDO-VOUT) x IOUT              | 100 mW                   |       |
| VBB    | Threshold Reference Input Voltage                                      | -4.0 V to +0.5 V         |       |
| IBB    | Input current (from interfacing family)                                | -0.5 mA to +1.0 mA       |       |
| VTTC   | VH/VL Internal Decoupling Cap. Return                                  | -6.0 V to VL             |       |
| VTT    | Load Termination Supply  | -6.0 V to VDD + 6.0 V    |       |
| VH-VL  | Output Voltage Amplitude   | 7V                       |       |

## Notes:

- All voltages specified with VDD defined as Gnd. Positive current is defined as current into the device.
- TC is measured at case top.
- Subject to IOUT and power dissipation limitations.
- Power supply sequencing is not necessary, but since the VEE supply is used to bias off the normally-on depletion mode transistors, sustained (>5 secs.) application of VSS in the absence of VEE may result in excessive power dissipation and damage to the device.
- Voltage applied through a 42Ω series resistor.

### RECOMMENDED OPERATING CONDITIONS (Note 3)

| SYMBOL  | PARAMETER                  | MIN  | TYP    | MAX  | UNITS | NOTES |
|---------|----------------------------|------|--------|------|-------|-------|
| TC      | Case Operating Temperature | 25   |        | 60   | °C    | 1     |
| VDD     | Supply Voltage             |      | Gnd    |      | V     |       |
| VCC     | Supply Voltage             | +3   | VH + 2 | 7.5  | V     |       |
| VSS     | Supply Voltage             | -3.5 | -3.4   | -3.3 | V     |       |
| VEE     | Supply Voltage             | -5.5 | -5.2   | -5.1 | V     |       |
| VH      | High level set voltage     | -1.1 |        | 5.5  | V     |       |
| VL      | Low level set voltage      | -2.5 |        | 1.5  | V     |       |
| VH - VL | Output voltage amplitude   | 0    |        | 5.5  | V     | 2     |

## Notes:

- Case measured at case top. **User attention to device thermal management is recommended.** See GigaBit Application Note 3, "Thermal Management of PicoLogic and NanoRam GaAs Digital IC Families" for a complete discussion of all aspects of device thermal management. Heatsinks are available from GigaBit.
- For series terminations. For shunt termination:  $V_{oh} = V_H \times \left( \frac{R_t}{R_t + R_{on}} \right)$ ;  $V_{ol} = V_L \times \left( \frac{R_t}{R_t + R_{on}} \right)$ ;  $R_t$ : termination resistance.
- Max. safe voltage applied to any output through a 42Ω series resistor is limited to VL to VL + 7.0V.



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**DC CHARACTERISTICS** (DC to 500 MHz - Note 1)

Tc = 25°C to 60°C, Vss = -3.5V to -3.3V, Vee = -5.5V to -5.1V, Vcc = 3.0V (ECL) or 7.0V (TTL), Vdd = Gnd

| Symbol  | Parameter                         | Min      | Typ  | Max      | Units | Test Conditions          | Notes |
|---------|-----------------------------------|----------|------|----------|-------|--------------------------|-------|
| Vih     | Input voltage high                | -1.0     |      | Vdd      | V     |                          |       |
| Vil     | Input voltage low                 | Vss      |      | -1.6     | V     |                          |       |
| Vcm     | Common mode Vin                   | -1.9     | VBB  | -0.5     | V     |                          |       |
| Iin     | Input current                     | -500     |      | 500      | µA    | Vin = -0.5V to -1.9V     |       |
| Vbbs    | Threshold Ref. voltage (ECL/GaAs) | -1.05    | -1.2 | -1.4     | V     |                          | 3     |
| Voh     | Output voltage high               | VH - .02 | VH   | VH       | V     | No DC load, VH-VL ≤ 5.5V |       |
| Vol     | Output voltage low                | VL       | VL   | VL + .02 | V     | No DC load, VH-VL ≤ 5.5V |       |
| Ioh     | Output drive current              |          | ±100 |          | mA    |                          | 2     |
| Ron     | Driver FET on rest.               | 6.5      | 8    | 9.5      | Ω     | At Voh, Vol              |       |
| Voffset | Input Offset Voltage              |          | 50   |          | mV    |                          |       |
| ICC     | Supply Current                    |          | 120  |          | mA    |                          |       |
| IEE     | Supply Current                    |          | 140  |          | mA    |                          |       |
| ISS     | Supply Current                    |          | 65   |          | mA    |                          |       |
| PdE     | Power Dissipation                 |          | 1.2  |          | W     | VCC = 2.0V (ECL)         | 4     |
| PdT     | Power Dissipation                 |          | 1.8  |          | W     | VCC = 7.0V (TTL)         | 4     |
| Izl     | Three state output leakage        |          | ±40  |          | µA    | @40°C                    | 5     |

- Notes:**
1. Test conditions unless otherwise indicated: -D input = -1.30V.
  2. Test Conditions: VH - Vout ≥ 1V; VL - Vout ≤ -1.0V.
  3. Source Impedance = 40Ω nominally. ΔVBB/ΔTemp. = +0.6mV/°C; ΔVBB/ΔVSS = +0.2mV/mV.
  4. Measured at nominal supply voltages, 50% output duty cycle and both drivers powered.
  5. Voh=2.7V, Vol=0.4V

**AC CHARACTERISTICS** (Note 1, 2)

Tc = 25°C to 60°C, Vss = -3.5V to -3.3V, Vee = -5.5V to -5.1V, Vcc = 2.0V (ECL) or 7.0V (TTL), Vdd = Gnd

| Symbol  | Parameter                         | ECL/GaAs Output Levels |              |     | TTL Output Levels |             |     | Units | Test Cond. | Notes |
|---------|-----------------------------------|------------------------|--------------|-----|-------------------|-------------|-----|-------|------------|-------|
|         |                                   | Min                    | Typ          | Max | Min               | Typ         | Max |       |            |       |
| F       | Operating frequency               | 1000                   | 1500         |     | 300               | 500         |     | MHz   |            |       |
| td      | Propagation delay                 |                        | 600          |     |                   | 700         |     | ps    | ERC = VSS  |       |
| tds     | Prop. delay, slow edge rates      |                        | 1500         |     |                   | 1500        |     | ps    | ERC = VEE  |       |
| td3     | 3-state delay                     |                        | 750          |     |                   | 850         |     | ps    | ERC = VSS  |       |
| td3s    | 3-state delay, slow edge rates    |                        | 1500         |     |                   | 1500        |     | ps    | ERC = VEE  |       |
| Δtdm    | Prop. Delay match; H-L, L-H       |                        | 50           | 100 |                   | 50          | 100 | ps    | ERC = VSS  |       |
| Δtdms   | ΔProp. Delay match, slow mode     |                        | 300          |     |                   | 300         |     | ps    | ERC = VEE  |       |
| Δtd/Δdc | Δ Prop. delay with duty cycle     |                        | ±100         |     |                   | ±100        |     | ps    | ERC = VSS  |       |
| Δtd/ΔT  | Prop. delay temp. coeff.          |                        | ±1.0         |     |                   | ±1.0        |     | ps/°C | or VEE     |       |
| T       | Output slew rate                  |                        | 7            |     |                   | 25          |     | V/ns  | ERC = VSS  | 3     |
| Tr,f    | Output rise and fall times        |                        | 150          |     |                   | 200         |     | ps    | ERC = VSS  |       |
| Ts      | Slow Output slew rate             |                        | 0.7          |     |                   | 2.5         |     | V/ns  | ERC = VEE  | 3     |
| Tsr,sf  | Slow Output rise and fall times   |                        | 1500         |     |                   | 2000        |     | ps    | ERC = VEE  |       |
| Tset    | Settling time to 0.05 (Voh - Vol) |                        | 0.2          | 1.0 |                   | 0.2         | 1.0 | ns    |            |       |
| W       | Output crosstalk                  |                        | .05(Voh-Vol) |     |                   | 05(Voh-Vol) |     | V     | @ 100MHz   |       |

- Notes:**
1. VBB = -1.3V, Vih = -1.0V, Vil = -1.6V.
  2. ECL Vp-p output = 1.0V; TTL Vp-p output = 5.0V.
  3. Output rise and fall times are measured at 10% and 90% points.



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16G061A

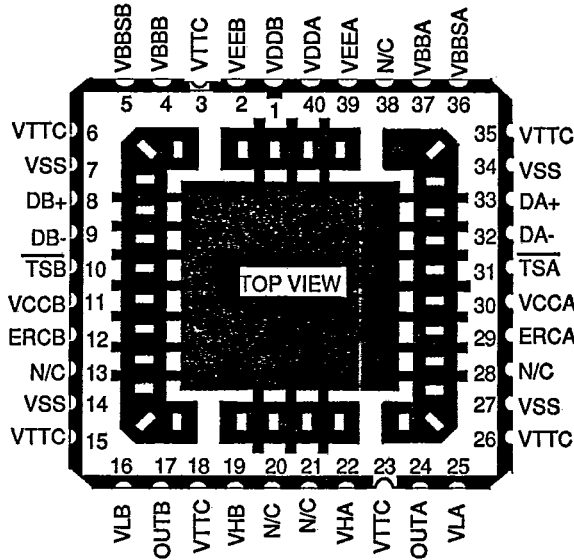
ADVANCE

T-52-07

PIN DESCRIPTIONS

|            |  |                  |   |
|------------|--|------------------|---|
| DA+, DA-   | Differential data inputs A.  | VTTC             | AC return pin for the package-internal decoupling capacitors tied to VH (VHigh) and VL (VLow) pins. For proper decoupling, VTTC should be tied to a voltage no more positive than VLow. When driving TTL/CMOS levels, VTTC = DUT ground is appropriate. When driving ECL/GaAs levels, VTTC should be connected to the DUT output termination voltage ( DUT VTT ). Connecting VTTC to the termination voltage associated with the 16G061A input signal may couple noise to the output. |
| DB+, DB-   | Differential data inputs B.  |                  |   |
| OA, OB     | Output A, Output B.  |                  |   |
| VLA, VLB   | Output Low level set voltages.   |                  |   |
| VHA, VHB   | Output High level set voltages.  |                  |   |
| TSA, TSB   | Three-State output controls. Output, OA or OB, is forced into a high impedance condition when TSA or TSB respectively is low.  |                  |   |
| ERCA, ERCA | Edge Rate Controls. Output Edge rates are continuously slowed when ERC is moved from VSS to VEE. Fast edge rates are obtained when ERC is tied to VSS. Slow edge rates are obtained when ERC is tied to VEE. | VBBA, VBBA, VBBA | Reference input to the 10G061A's input threshold compensation circuit. Connect to the VBB supplied from ECL when driving from ECL. <u>Otherwise connect to corresponding VBBS pin.</u>  |
| VDDA, VDDB | Ground Pins (0V).  |                  |   |
| VSS        | - 3.4V power supplies.   |                  |   |
| VEEA, VEEB | - 5.2V power supplies.   |                  |   |
| VCCA, VCCB | Positive power supplies. Nominally VH + 2V.  | VBBSA, VBBSB     | Picologic Threshold reference output voltage. Connect to VBB when driving from PicoLogic $\Delta VBBS/\Delta Temp = 0.6mV/^{\circ}C$ , $\Delta VBBS/\Delta VSS = 0.2 mV/mV$ .   |

Pin Function Drawing  
Package Types "L" and "C"



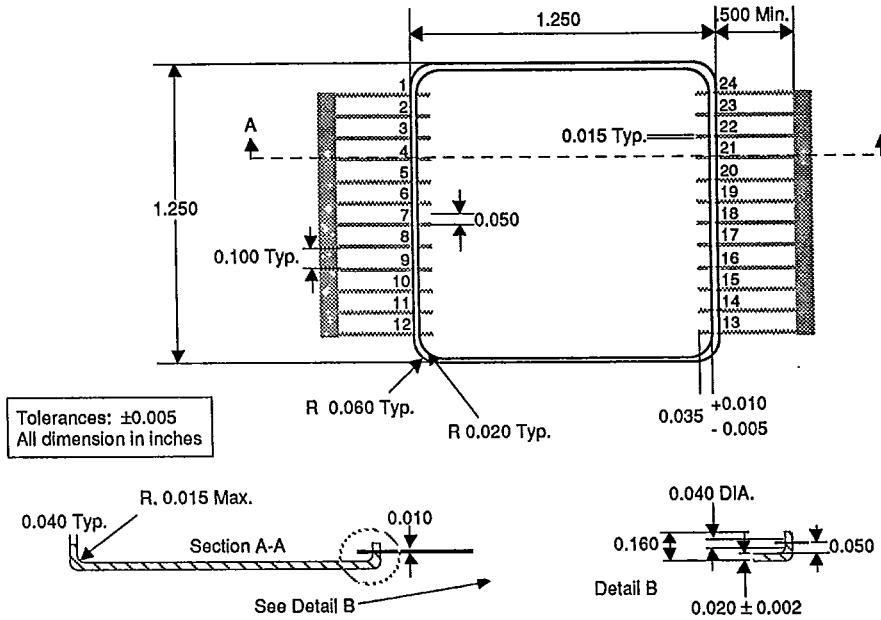


**24 PIN HYBRID  
18 PIN PACKAGE**

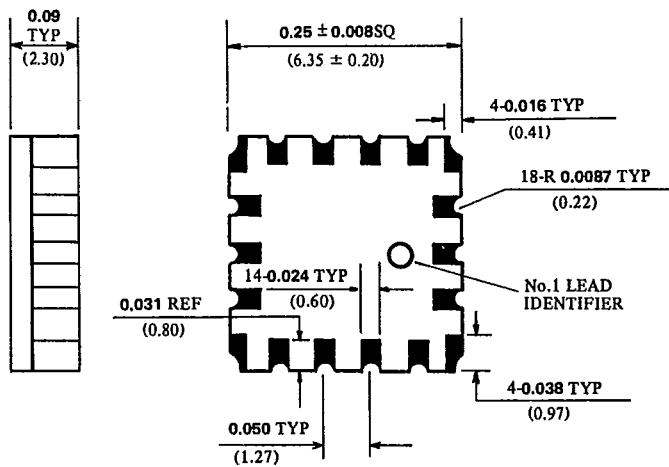
T-90-20

**24 PIN HYBRID PACKAGE**

Type H



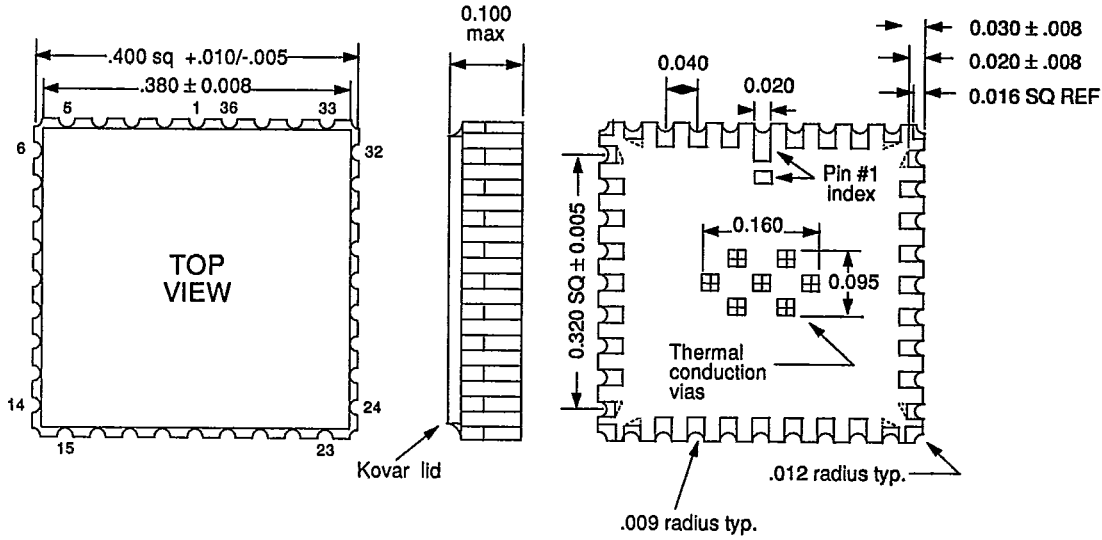
**18 PIN LEADLESS CHIP CARRIER  
TYPE L1**



All dimensions shown in inches and (millimeters)



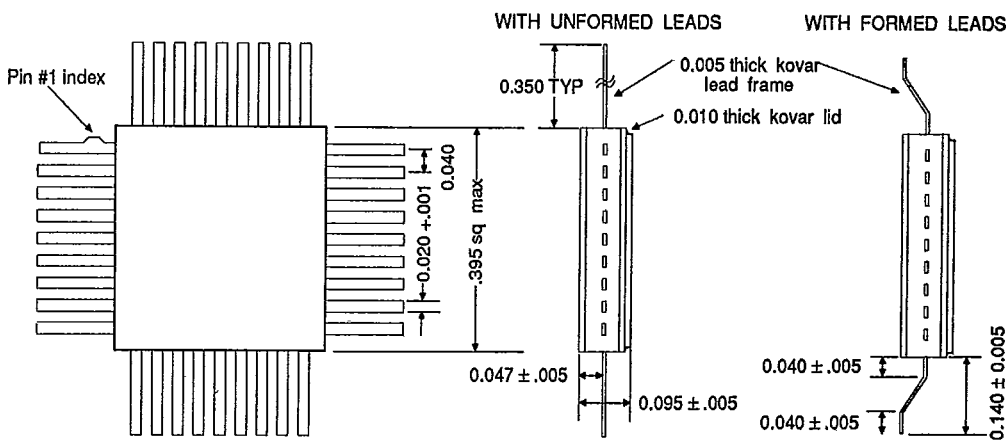
**36 PIN LEADLESS CHIP CARRIER  
TYPE L36**



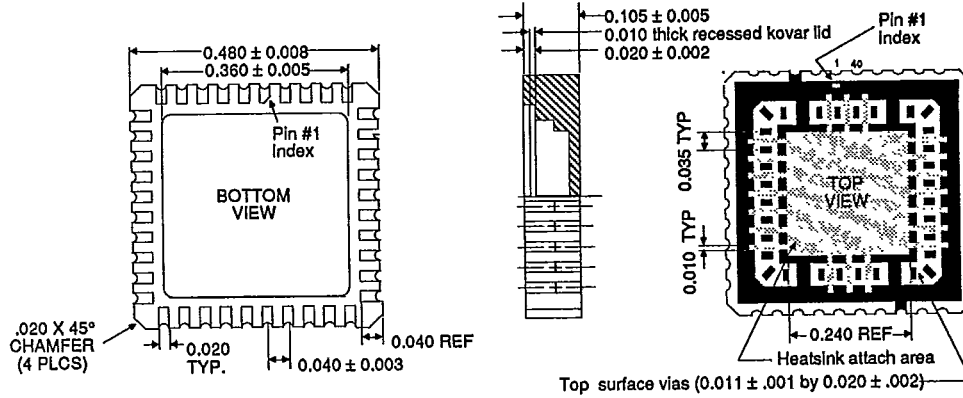
**NOTES:**

- 1) The package bottom thermal vias, top lid surface and 4 metallized corner castellations (when present) are all at V<sub>SS</sub> potential.
- 2) All dimensions in inches.
- 3) Pin #1 identifier may be an elongated pad or small, square gray marker.

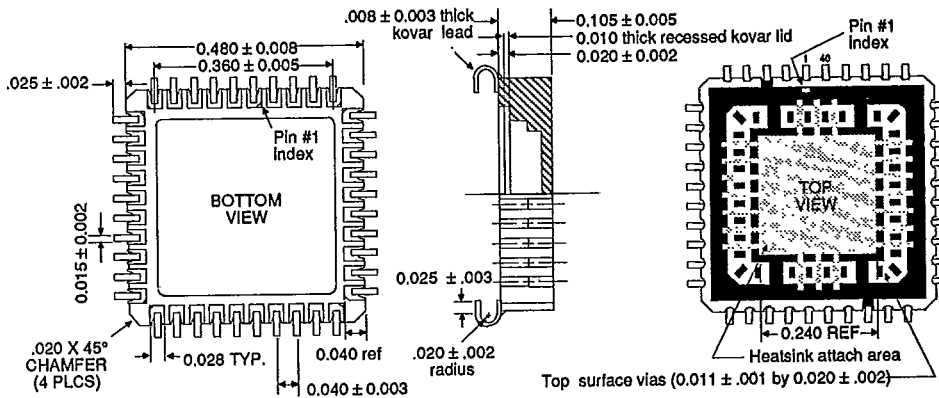
**36 I/O LEAD FLATPACK  
TYPE F**



**40 PIN LEADLESS CHIP CARRIER**  
**TYPE L**



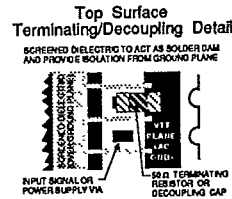
**40 PIN LEADED CHIP CARRIER**  
**TYPE C**



**NOTES:**

- (1) Footprint is JEDEC standard outline.
- (2) Top surface vias (for terminating resistors and decoupling capacitors) are not available on pins 3, 4, 17, 18, 23, 24, 37 and 38.
- (3) Top surface metal (not including vias) and pins 3 and 23 are fixed at VTT potential.
- (4) Recommended top surface chip resistors are 0.040 long by 0.020 wide by 0.010 thick typ, 100 mw min. nominal power rating (Mini-Systems MSR-21 or equivalent).
- (5) Recommended top surface chip capacitors are 0.040 long by 0.030 wide by 0.020 thick typ, 25V VDDW, 1000 pf. min. (Johnson R02 case or equivalent).
- (6) Recommended heatsinks are GBL P/Ns 90GHS-40-A and 90GHS-40-B.
- (7) Thermally conductive, electrically non-conductive epoxy is recommended for heatsink attachment (Ablestick 789-4 or 501K, or Thermalloy Thermalbond™ or equivalent).
- (8) L40 and C40 packages are dimensionally identical except for contact finger width.

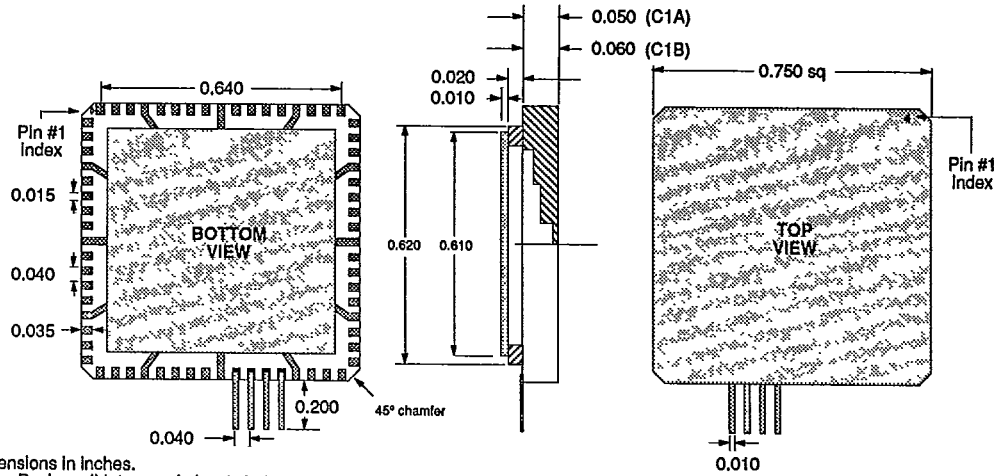
| TOP SURFACE LEGEND:      |   |
|--------------------------|---|
| Metalized Ceramic.....   | ■ |
| Screened Dielectric..... | ▨ |
| Bare Ceramic.....        | □ |





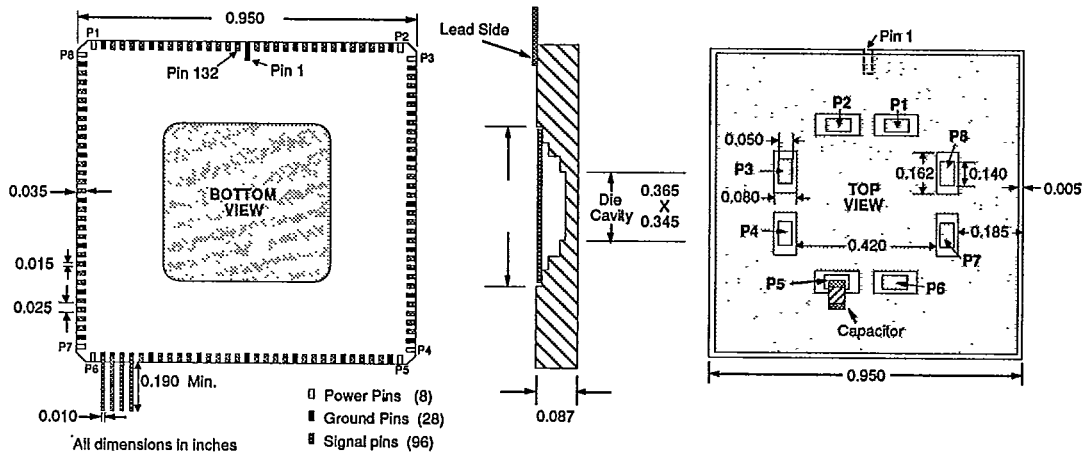
**68 & 132 PIN  
PACKAGES  
T-90-20**

**68 PIN LEADED CHIP CARRIER  
TYPE C1**



- (1) All dimensions in inches.
- (2) a. C1A: Package lid, top, and pins 4, 9, 14, 21, 26, 31, 38, 43, 48, 55, 60, 65 are at common potential (system ground).
- b. C1B: Package lid and pins 4, 9, 14, 21, 26, 31, 38, 43, 48, 55, 60, 65 are at common potential (system ground).

**132 PIN LEADED CHIP CARRIER  
TYPE C3**



**11**